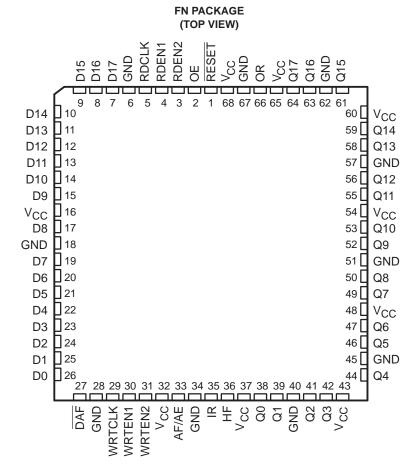
- Member of the Texas Instruments Widebus™ Family
- Independent Asynchronous Inputs and Outputs
- Read and Write Operations Can Be Synchronized to Independent System Clocks
- Programmable Almost-Full/Almost-Empty Flag
- Pin-to-Pin Compatible With SN74ACT7881 and SN74ACT7811

- Input-Ready, Output-Ready, and Half-Full Flags
- Cascadable in Word Width and/or Word Depth (See Application Information)
- Fast Access Times of 11 ns With a 50-pF Load
- High Output Drive for Direct Bus Interface
- Package Options Include 68-Pin Plastic Leaded Chip Carriers (FN) or 80-Pin Shrink Quad Flat (PN) Package





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

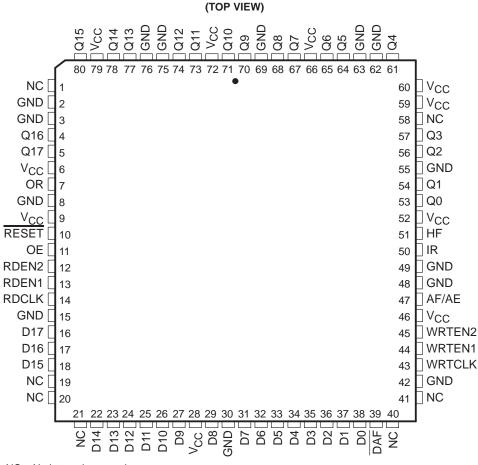
Widebus is a trademark of Texas Instruments Incorporated

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



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### SN74ACT7882 2048 × 18 CLOCKED FIRST-IN, FIRST-OUT MEMORY SCAS445C - JUNE 1994 - REVISED APRIL 1998



**PN PACKAGE** 

NC - No internal connection

### description

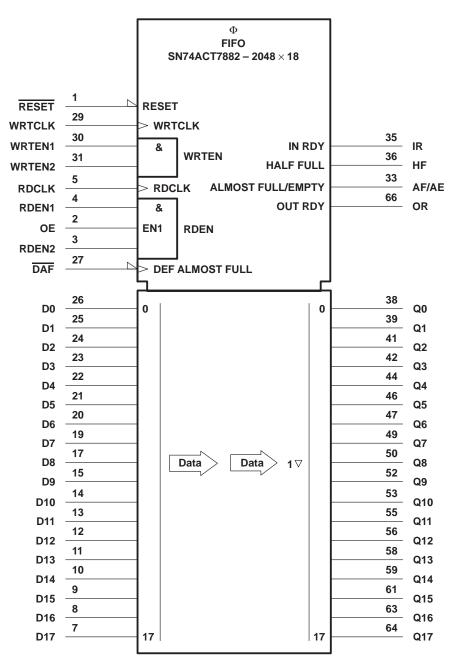
A FIFO memory is a storage device that allows data to be written into and read from its array at independent data rates. The SN74ACT7882 is organized as 2048 bits deep  $\times$  18 bits wide. The SN74ACT7882 processes data at rates up to 67 MHz and access times of 11 ns in a bit-parallel format. Data outputs are noninverting with respect to the data inputs. Expansion is accomplished easily in both word width and word depth.

The SN74ACT7882 has normal input-bus to output-bus asynchronous operation. The special enable circuitry adds the ability to synchronize independent reads and writes to their respective system clocks.

The SN74ACT7882 is characterized for operation from 0°C to 70°C.



### logic symbol<sup>†</sup>

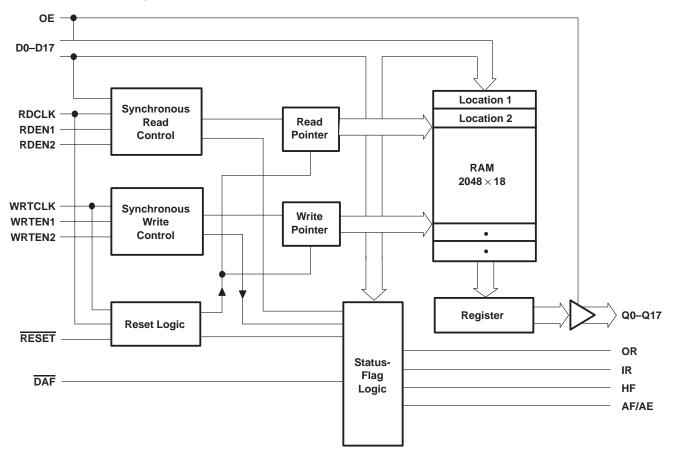


<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the FN package.



### SN74ACT7882 2048 × 18 CLOCKED FIRST-IN, FIRST-OUT MEMORY SCAS445C - JUNE 1994 - REVISED APRIL 1998

### functional block diagram





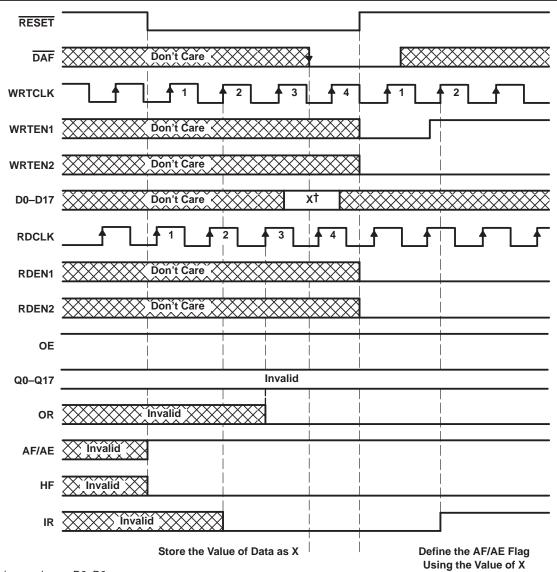
### **Terminal Functions<sup>†</sup>**

		110	DESCRIPTION					
NAME	NO.	1/0	DESCRIPTION					
AF/AE	33	0	Almost-full/almost-empty flag. The AF/AE boundary is defined by the AF/AE offset value (X). This value can be programmed during reset or the default value of 256 can be used. AF/AE is high when the number of words in memory is less than or equal to X. AF/AE also is high when the number of words in memory is greater than or equal to (2048 – X). Programming the AF/AE offset value (X) is accomplished during a reset cycle. The AF/AE offset value (X) is either user-defined or the default value of X = 256. The procedure to program AF/AE is as follows: <b>User-defined X</b> Step 1: Take DAF from high to low. The high-to-low transition of DAF input stores the binary value on the data inputs as X. The following bits are used, listed from most significant bit to least significant bit D9–D0. Step 2: If RESET is not already low, take RESET low. Step 3: With DAF held low, take RESET high. This defines the AF/AE using X. NOTE: To retain the current (X) offset, keep DAF low during subsequent reset cycles. <b>Default X</b> To redefine AF/AE using the default value of X = 256, hold DAF high during the reset cycle.					
DAF	27	I	Define almost-full. The high-to-low transition of DAF stores the binary value of data inputs as the AF/AE offset value (X). With DAF held low, a RESET cycle defines the AF/AE flag using X.					
D0–D17	26–19, 17, 15–7	I	Data inputs for 18-bit-wide data to be stored in the memory. A high-to-low transition on $\overline{\text{DAF}}$ captures data for the almost-empty/almost-full offset (X) from D9–D0.					
HF	36	0	Half-full flag. HF is high when the FIFO contains 1024 or more words and is low when the number of words in memory is less than half the depth of the FIFO.					
IR	35	0	Input-ready flag. IR is high when the FIFO is not full and low when the device is full. During reset, IR is driven low on the rising edge of the second WRTCLK pulse. IR then is driven high on the rising edge of the second WRTCLK pulse after RESET goes high. After the FIFO is filled and IR is driven low, IR is driven high on the second WRTCLK pulse after the first valid read.					
OE	2	I	Output enable. The Q0–Q17 outputs are in the high-impedance state when OE is low. OE must be high before the rising edge of RDCLK to read a word from memory.					
OR	66	0	Output-ready flag. OR is high when the FIFO is not empty and low when it is empty. During reset, OR is set low on the rising edge of the third RDCLK pulse. OR is set high on the rising edge of the third RDCLK pulse to occur after the first word is written into the FIFO. OR is set low on the rising edge of the first RDCLK pulse after the last word is read.					
Q0–Q17	38–39, 41–42, 44, 46–47, 49–50, 52–53, 55–56, 58–59, 61, 63–64	0	Data out. The first data word to be loaded into the FIFO is moved to Q0–Q17 on the rising edge of the third RDCLK pulse to occur after the first valid write. RDEN1 and RDEN2 do not affect this operation. Following data is unloaded on the rising edge of RDCLK when RDEN1, RDEN2, OE, and OR are high.					
RDCLK	5	I	Read clock. Data is read out of memory on the low-to-high transition at RDCLK if OR, OE, and RDEN1 and RDEN2 are high. RDCLK is a free-running clock and functions as the synchronizing clock for all data transfers out of the FIFO. OR also is driven synchronously with respect to RDCLK.					
RDEN1 RDEN2	4 3	I	Read enable. RDEN1 and RDEN2 must be high before a rising edge on RDCLK to read a word out of memory. RDEN1 and RDEN2 are not used to read the first word stored in memory.					
RESET	1	I	Reset. A reset is accomplished by taking $\overrightarrow{RESET}$ low and generating a minimum of four RDCLK and WRTCLK cycles. This ensures that the internal read and write pointers are reset and that OR, HF, and IR are low, and AF/AE is high. The FIFO must be reset upon power up. With $\overrightarrow{DAF}$ at a low level, a low pulse on $\overrightarrow{RESET}$ defines $\overrightarrow{AF/AE}$ using the $\overrightarrow{AF/AE}$ offset value (X), where X is the value previously stored. $\overrightarrow{DAF}$ held high during a $\overrightarrow{RESET}$ cycle defines the $\overrightarrow{AF/AE}$ flag using the default value of X = 256.					
WRTCLK	29	I	Write clock. Data is written into memory on a low-to-high transition of WRTCLK if IR, WRTEN1, and WRTEN2 are high. WRTCLK is a free-running clock and functions as the synchronizing clock for all data transfers into the FIFO. IR also is driven synchronously with respect to WRTCLK.					
WRTEN1 WRTEN2	30 31	I	Write enable. WRTEN1 and WRTEN2 must be high before a rising edge on WRTCLK for a word to be written into memory. WRTEN1 and WRTEN2 do not affect the storage of the AF/AE offset value (X).					

<sup>†</sup> Terminals listed are for the FN package.



# SN74ACT7882 $2048 \times 18$ CLOCKED FIRST-IN, FIRST-OUT MEMORY SCAS445C – JUNE 1994 – REVISED APRIL 1998



<sup>†</sup> X is the binary value on D9–D0.

Figure 1. Reset Cycle: Define AF/AE Using a Programmed Value of X



# SN74ACT7882 $2048 \times 18$ CLOCKED FIRST-IN, FIRST-OUT MEMORY SCAS445C – JUNE 1994 – REVISED APRIL 1998

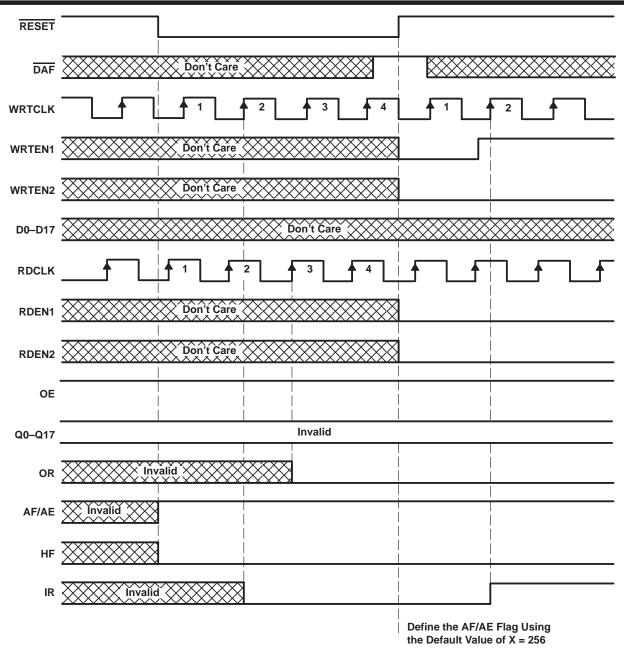


Figure 2. Reset Cycle: Define AF/AE Using the Default Value



# SN74ACT7882 2048 imes 18CLOCKED FIRST-IN, FIRST-OUT MEMORY SCAS445C – JUNE 1994 – REVISED APRIL 1998

RESET

DAF	Don't Care
WRTCLK	
WRTEN1	
WRTEN2	
D0-D17	W1   W2   W3   W4   Symptotic Symptom   Sympon   Sympon   Symptom
RDCLK	
RDEN1	
RDEN2	
OE	
Q0–Q17	Invalid W1
OR	
AF/AE	
HF	
IR	

DATA-WORD NUMBERS FOR FLAG TRANSITIONS

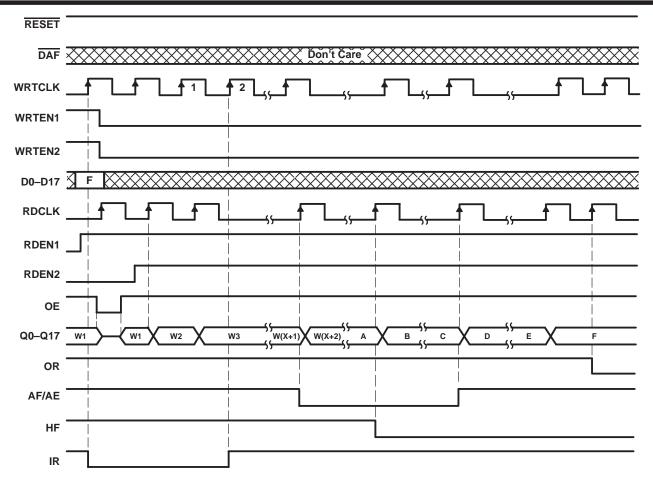
	TRANSITION WORD							
	Α	С						
ĺ	W1025	W(2049 - X)	W20495					

Figure 3. Write



# SN74ACT7882 $2048 \times 18$ CLOCKED FIRST-IN, FIRST-OUT MEMORY SCAS445C – JUNE 1994 – REVISED APRIL 1998





#### DATA-WORD NUMBERS FOR FLAG TRANSITIONS

TRANSITION WORD								
A B C D E F								
W1025	W1030	W(2048 – X)	W(2049 – X)	W2048	W2049			

Figure 4. Read



# SN74ACT7882 2048 × 18 CLOCKED FIRST-IN, FIRST-OUT MEMORY SCAS445C – JUNE 1994 – REVISED APRIL 1998

### absolute maximum ratings over operating free-air temperature range<sup>†</sup>

Supply voltage range, V <sub>CC</sub> Input voltage range, V <sub>I</sub>	
Voltage range applied to a disabled 3-state output Package thermal impedance, θ <sub>IA</sub> (see Note 1): FN package	–0.5 V to 5.5 V
PN package	62°C/W
Storage temperature range, T <sub>stg</sub>	. −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: The package thermal impedance is calculated in accordance with JESD 51.

### recommended operating conditions

		MIN	MAX	UNIT
VCC	Supply voltage	4.5	5.5	V
VIH	High-level input voltage	2		V
VIL	Low-level input voltage		0.8	V
IOH	High-level output current		-8	mA
IOL	Low-level output current		16	mA
Т <sub>А</sub>	Operating free-air temperature	0	70	°C

### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	Т	MIN	TYP <sup>‡</sup>	MAX	UNIT	
VOH	$V_{CC} = 4.5 V,$	I <sub>OH</sub> = -8 mA	2.4			V
V <sub>OL</sub>	$V_{CC} = 4.5 V,$	I <sub>OL</sub> = 16 mA			0.5	V
lj	$V_{CC} = 5.5 V,$	$V_{I} = V_{CC} \text{ or } 0$			±5	μA
I <sub>OZ</sub>	$V_{CC} = 5.5 V,$	$V_{O} = V_{CC} \text{ or } 0$			±5	μA
8	$V_{I} = V_{CC} - 0.2 V \text{ or } 0$				400	μA
<sup>I</sup> CC <sup>§</sup>	One input at 3.4 V,	Other inputs at $V_{CC}$ or GND			1	mA
Ci	$V_{  } = 0,$	f = 1 MHz		4		pF
Co	$V_{O} = 0,$	f = 1 MHz		8		pF

<sup>‡</sup> All typical values are at  $V_{CC} = 5 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

§ ICC is tested with outputs open.



### SN74ACT7882 2048 × 18 CLOCKED FIRST-IN, FIRST-OUT MEMORY SCAS445C - JUNE 1994 - REVISED APRIL 1998

# timing requirements over recommended ranges of supply voltage and operating free-air temperature (see Figures 1 through 5)

			'ACT78	882-15	'ACT78	82-20	'ACT78	82-30	UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	UNIT
fclock	Clock frequency			67		50		33.4	MHz
		WRTCLK high	5		7		8.5		
		WRTCLK low	6		7		11		
tw	Pulse duration	RDCLK high	5		7		8.5		ns
		RDCLK low	6		7		11		
		DAF high (default AF/AE value)	7		8		10		
		Data in (D0–D17) before WRTCLK <sup>↑</sup>	5		5		5		
		WRTEN1, WRTEN2 high before WRTCLK1	4		5		5		
		OE, RDEN1, RDEN2 high before RDCLK↑	4		5		5		
t <sub>su</sub>	Setup time	Reset: RESET low before first WRTCLK <sup>↑</sup> and RDCLK <sup>↑†</sup>	5		6		7		ns
		Define AF/AE: D0–D9 before DAF↓	5		5		5		
		Define AF/AE: DAF↓ before RESET↑	4		6		7		
		Define AF/AE (default): DAF high before RESET↑	4		5		5		
		Data in (D0–D17) after WRTCLK↑	0		0		0		
		WRTEN1, WRTEN2 high after WRTCLK1	0		0		0		
		OE, RDEN1, RDEN2 high after RDCLK <sup>↑</sup>	0		0		1		
t <sub>h</sub>	Hold time	Reset: RESET low after fourth WRTCLK1 and RDCLK11	0		0		0		ns
		Define AF/AE: D0–D9 after $\overline{DAF}\downarrow$	0		0		0		
		Define AF/AE: DAF low after RESET↑	0		0		0		
		Define AF/AE (default): DAF high after RESET↑	0		0		0		

<sup>†</sup> To permit the clock pulse to be utilized for reset purposes

# switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $C_L = 50 \text{ pF}$ (unless otherwise noted) (see Figure 5)

FROM	ТО	'ACT78	382-15	'ACT78	82-20	'ACT78	82-30	
(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
WRTCLK or RDCLK		67		50		33.4		MHz
RDCLK↑	Any Q	3	12	3	13	3	18	ns
RDCLK↑	Any Q							
WRTCLK↑	IR	2	8	2	9.5	2	12	
RDCLK↑	OR	2	8	2	9.5	2	12	ns
WRTCLK↑		6	17	6	19	6	22	
RDCLK↑	AF/AE	6	17	6	19	6	22	
WRTCLK↑	HF	6	14	6	17	6	21	ns
RDCLK↑	HF	6	14	6	17	6	21	ns
RESET↓	AF/AE	3	12	3	17	3	21	ns
RESET↓	HF	3	14	3	19	3	23	ns
OE	Any Q	2	9	2	11	2	11	ns
OE	Any Q	2	10	2	14	2	14	ns
	(INPUT)   WRTCLK or RDCLK   RDCLK↑   WRTCLK↑   RDCLK↑   WRTCLK↑   RDCLK↑   WRTCLK↑   RDCLK↑   RDCLK↑   RDCLK↑   RDCLK↑   RESET↓   RESET↓   OE	(INPUT)(OUTPUT)WRTCLK or RDCLKRDCLK↑Any QRDCLK↑MRTCLK↑RDCLK↑ORWRTCLK↑RDCLK↑WRTCLK↑HFRDCLK↑HFRDCLK↑HFRESET↓AF/AEOEAny Q	(INPUT)(OUTPUT)MINWRTCLK or RDCLK67RDCLK^Any QRDCLK^Any QWRTCLK^IRQRDCLK^WRTCLK^ORRDCLK^AF/AERDCLK^6RDCLK^HF6RDCLK^HF6RDCLK^HF6RDCLK^HF6RDCLK^HF7AF/AE8RESET↓9AF/AE9AF/AE10AF/AE10AF/AE10AF/AE11AF/AE12AF/AE13RESET↓14Any Q15Any Q16Any Q	(INPUT)(OUTPUT)MINMAXWRTCLK or RDCLK6767RDCLKÎAny Q312RDCLKÎAny Q312WRTCLKÎIR28RDCLKÎOR28WRTCLKÎAF/AE617RDCLKÎHF614RDCLKÎHF614RDCLKÎHF312RESETJAF/AE312RESETJHF314OEAny Q29	INDUTIO (OUTPUT)MINMAXMINWRTCLK or RDCLK6750RDCLK $\uparrow$ Any Q3123RDCLK $\uparrow$ Any Q3123WRTCLK $\uparrow$ IR282WRTCLK $\uparrow$ OR282WRTCLK $\uparrow$ AF/AE6176RDCLK $\uparrow$ HF6146RDCLK $\uparrow$ HF6146RDCLK $\uparrow$ HF3123RESET $\downarrow$ AF/AE3123RESET $\downarrow$ HF3143OEAny Q292	INPUT)(OUTPUT)MINMAXMINMAXWRTCLK or RDCLK6750 $67$ 50 $67$ $50$ RDCLK $\uparrow$ Any Q312313RDCLK $\uparrow$ Any Q $3$ 123 $13$ WRTCLK $\uparrow$ IR282 $9.5$ RDCLK $\uparrow$ OR282 $9.5$ WRTCLK $\uparrow$ AF/AE617619RDCLK $\uparrow$ HF614617RDCLK $\uparrow$ HF614617RDCLK $\uparrow$ HF312317RESET $\downarrow$ AF/AE312319OEAny Q29211	INDIM   IO   MIN   MAX   MIN </td <td>INDUTIO (OUTPUT)MINMAXMINMAXMINMAXWRTCLK or RDCLK675033.4RDCLK<math>\uparrow</math>Any Q312313318RDCLK<math>\uparrow</math>Any Q</td>	INDUTIO (OUTPUT)MINMAXMINMAXMINMAXWRTCLK or RDCLK675033.4RDCLK $\uparrow$ Any Q312313318RDCLK $\uparrow$ Any Q

<sup>‡</sup> This parameter is measured with  $C_L = 30 \text{ pF}$  (see Figure 6).

### SN74ACT7882 2048 × 18 CLOCKED FIRST-IN, FIRST-OUT MEMORY

SCAS445C - JUNE 1994 - REVISED APRIL 1998

### operating characteristics, $V_{CC} = 5 V$ , $T_A = 25^{\circ}C$

	PARAMETER	TEST CO	TYP	UNIT	
Cpd	Power dissipation capacitance per 1K bits	C <sub>L</sub> = 50 pF,	f = 5 MHz	65	pF

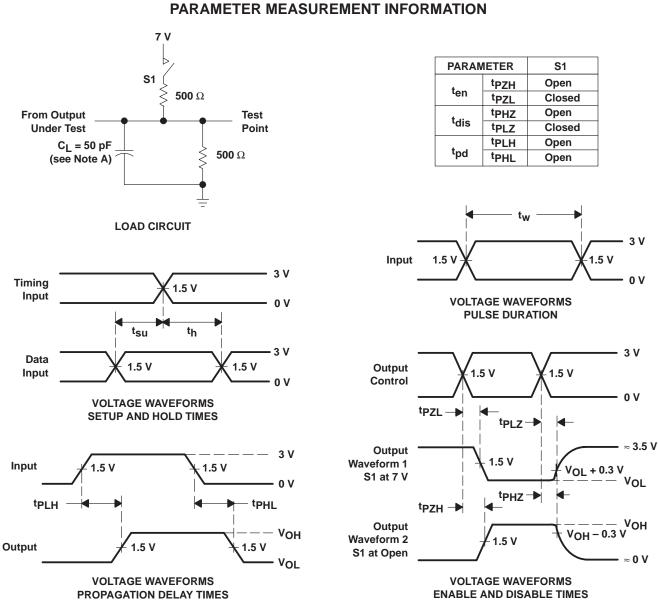
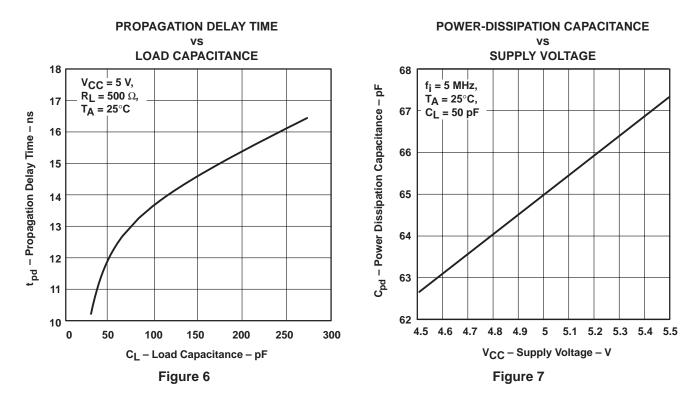




Figure 5. Load Circuit and Voltage Waveforms



### **TYPICAL CHARACTERISTICS**





### SN74ACT7882 2048 × 18 CLOCKED FIRST-IN, FIRST-OUT MEMORY SCAS445C – JUNE 1994 – REVISED APRIL 1998

### **APPLICATION INFORMATION**

### expanding the SN74ACT7882

The SN74ACT7882 is expandable in both word width and word depth. Word-depth expansion is accomplished by connecting the devices in series such that data flows through each device in the chain. Figure 8 shows two SN74ACT7882 devices configured for depth expansion. The common clock between the devices can be tied to either the write clock (WRTCLK) of the first device or the read clock (RDCLK) of the last device. The output-ready (OR) flag of the previous device and the input-ready (IR) flag of the next device maintain data flow to the last device in the chain whenever space is available.

Figure 9 is an example of two SN74ACT7882 devices in word-width expansion. Width expansion is accomplished by simply connecting all common control signals between the devices and creating composite IR and OR signals. The almost-full/almost-empty (AF/AE) flag and half-full (HF) flag can be sampled from any one device. Depth expansion and width expansion can be used together.

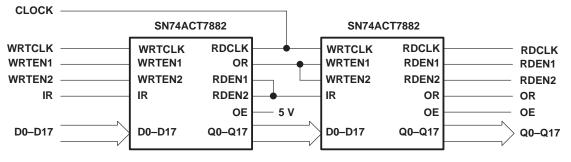


Figure 8. Word-Depth Expansion: 4096  $\times$  18 Bits

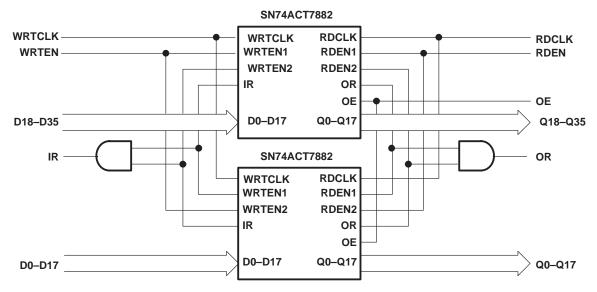


Figure 9. Word-Width Expansion: 2048  $\times$  36 Bits



### PACKAGING INFORMATION

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
SN74ACT7882-15FN	ACTIVE	PLCC	FN	68	18	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
SN74ACT7882-15PN	ACTIVE	LQFP	PN	80	119	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
SN74ACT7882-20FN	ACTIVE	PLCC	FN	68	18	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
SN74ACT7882-20PN	ACTIVE	LQFP	PN	80	119	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
SN74ACT7882-30FN	ACTIVE	PLCC	FN	68	18	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
SN74ACT7882-30PN	ACTIVE	LQFP	PN	80	119	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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# **MECHANICAL DATA**

MPLC004A - OCTOBER 1994

### PLASTIC J-LEADED CHIP CARRIER

### FN (S-PQCC-J\*\*)



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Falls within JEDEC MS-018

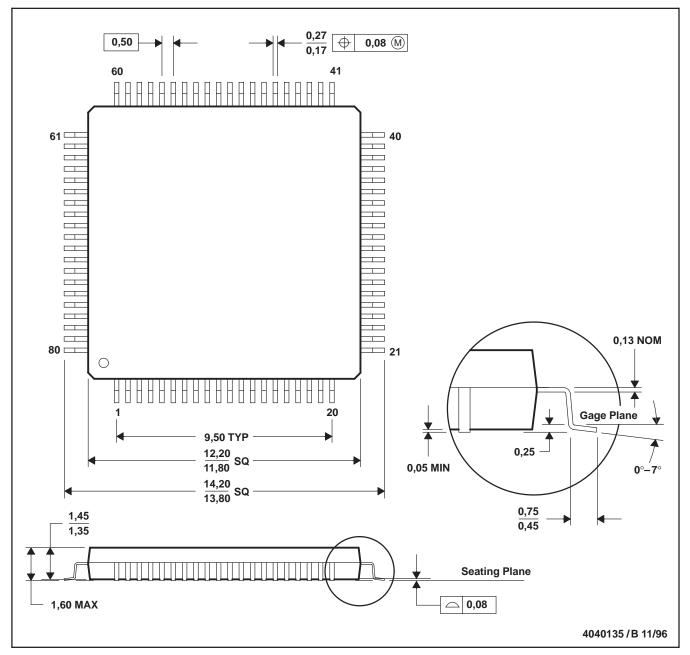


# **MECHANICAL DATA**

MTQF010A - JANUARY 1995 - REVISED DECEMBER 1996

### PN (S-PQFP-G80)

PLASTIC QUAD FLATPACK



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-026



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